TITLE: SILICON EMITTER WITH LOW POROSITY HEAVILY DOPED CONTACT LAYER INVENTOR: Xia Sheng et al.

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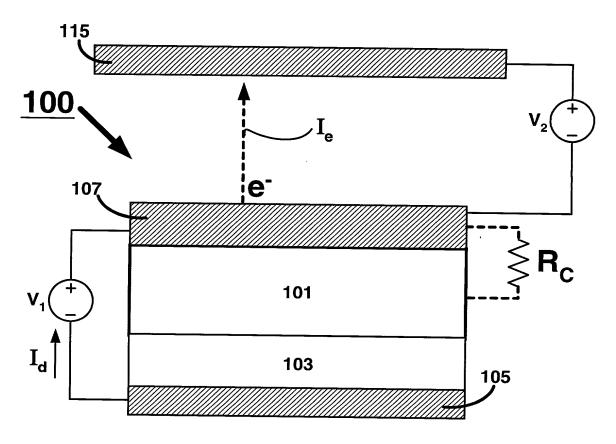
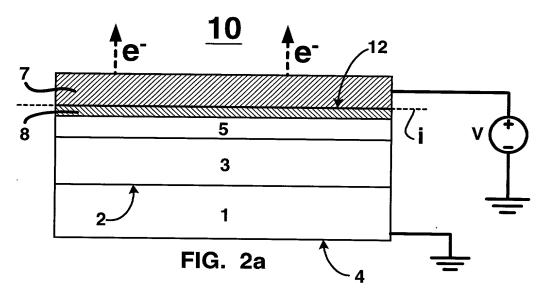
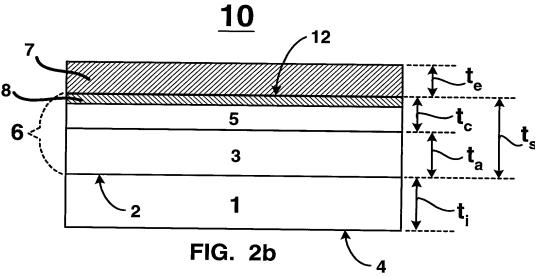


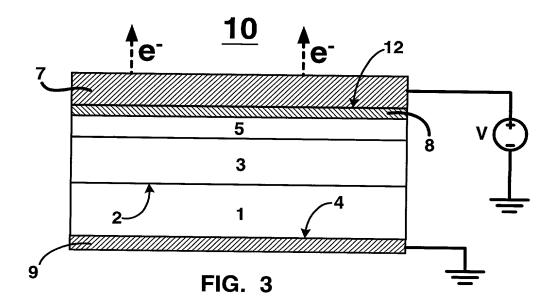
FIG. 1 (Prior Art)

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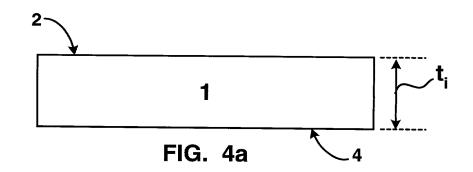
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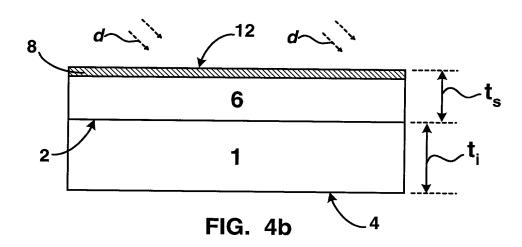


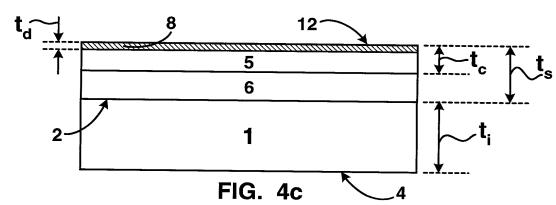


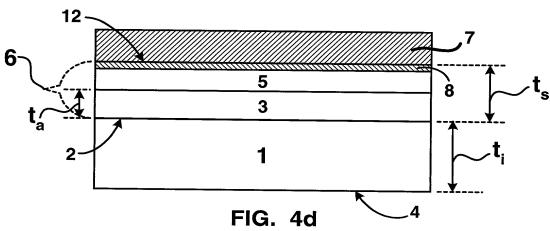


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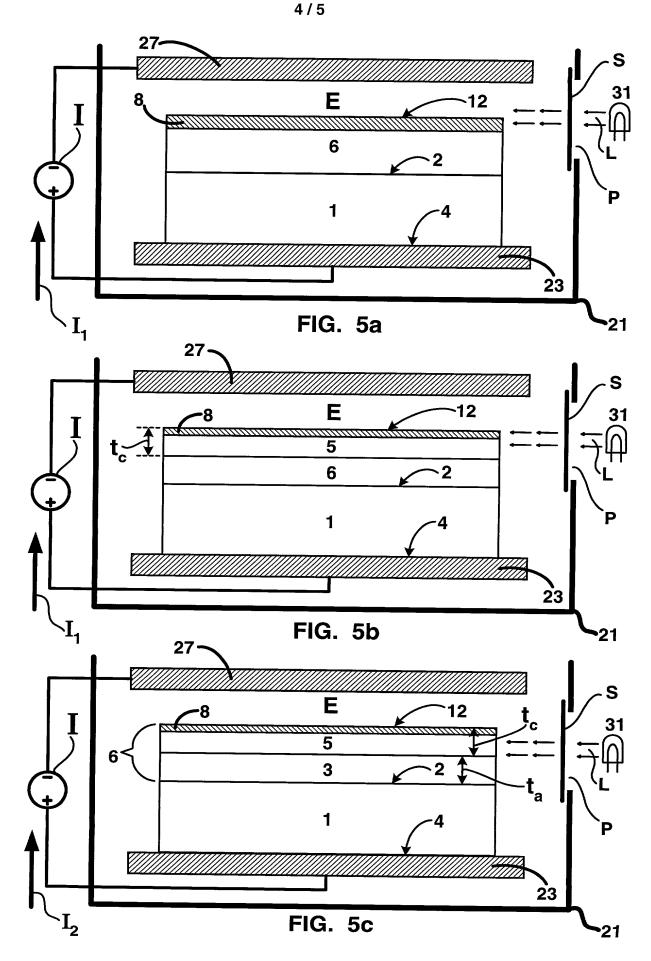






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